

APPENDIX A  
"CLEAN" VERSION OF EACH PARAGRAPH/SECTION/CLAIM  
37 C.F.R. § 1.121(b)(ii) AND (c)(i)

CLAIMS (with indication of amended or new):

*Sub 1*  
1 (Twice Amended) A MOS gated device which is resistant to single event radiation failure and having improved total dose radiation resistance; said device comprising:  
a P-type substrate having substantially flat, parallel upper and lower surfaces;  
a plurality of laterally spaced N-type body regions extending from said upper surface into said substrate  
at least one respective P-type source region formed in each of said body regions in said upper surface of said substrate and defining a respective channel region in said upper surface in said N-type body region;  
*CX* a gate electrode comprised of p-type polysilicon disposed atop and insulated from said channel region and operable to invert said channel region in response to the application of a suitable gate voltage to said gate electrode said gate being insulated from said channel region by a gate oxide layer comprising silicon dioxide, said gate oxide layer being radiation hardened and less than 1000Å thick; and  
a source electrode disposed atop said upper surface and connected to said at least one P-type source region.

*C 2/3 Sub 1 cont.*  
3. (Amended) The MOS gated device of claim 2 wherein said gate oxide has a thickness of between 500 to less than 1000Å.